

SiGe:C Low Noise Amplifier MMIC for LTE Rev. 1 — 19 May 2015

Product data sheet

#### **Product profile** 1.

### 1.1 General description

The BGU8L1UK is a Low Noise Amplifier (LNA) for LTE receiver applications. It comes as an extremely small and thin Wafer Level Chip Scale Package (WLCSP). The BGU8L1UK requires one external matching inductor.

The BGU8L1UK adapts itself to the changing environment resulting from co-habitation of different radio systems in modern cellular handsets. It has been designed for low power consumption and optimal performance. At low jamming power levels it delivers 16 dB gain at a noise figure of 0.7 dB. During high power levels, it temporarily increases its bias current to improve sensitivity.

The BGU8L1UK is optimized for 728 MHz to 960 MHz.

### 1.2 Features and benefits

- Operating frequency from 728 MHz to 960 MHz
- Noise figure (NF) = 0.7 dB
- Gain = 16 dB
- High input 1 dB compression point of -6 dBm
- High in band IP3<sub>i</sub> of 2 dBm
- Supply voltage 1.5 V to 3.1 V
- Self shielding package concept
- Integrated supply decoupling capacitor
- Optimized performance at a supply current of 4.7 mA
- Power-down mode current consumption < 1 μA</p>
- Integrated temperature stabilized bias for easy design
- Require only one input matching inductor
- Output DC decoupled
- ESD protection on all pins (HBM > 2 kV)
- Integrated matching for the output
- Extremely small Wafer Level Chip Scale Package (WLCSP) 0.65 × 0.44 × 0.2 mm; 6 solder bumps; 0.22 mm bump pitch
- 180 GHz transit frequency SiGe:C technology

### **1.3 Applications**

LNA for LTE reception in smart phones, feature phones, tablet PCs and RF front-end modules.



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### 1.4 Quick reference data

#### Table 1. Quick reference data

 $f = 882 \text{ MHz}; V_{CC} = 2.8 \text{ V}; V_{l(ENABLE)} \ge 0.8 \text{ V}; T_{amb} = 25 \text{ °C}; input matched to 50 \Omega using a 18 nH inductor; unless otherwise specified.}$ 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CC</sub>	supply voltage		1.5	-	3.1	V
I <sub>CC</sub>	supply current		-	4.7	-	mA
G <sub>p</sub>	power gain	[1]	-	16.0	-	dB
NF	noise figure	[1][2]	-	0.7	-	dB
P <sub>i(1dB)</sub>	input power at 1 dB gain compression	[1]	-	-6	-	dBm
IP3 <sub>i</sub>	input third-order intercept point	[1]	-	2	-	dBm

[1] E-UTRA operating band 5 (869 MHz to 894 MHz).

[2] PCB losses are subtracted.

## 2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
1	ENABLE		
2	RF_IN		15
3	GND_RF		2-4
4	RF_OUT	(2) (5)	
5	V <sub>CC</sub>		6 3 aaa-015193
6	GND		
		Bump side view	

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package	lackage						
	Name	Description	Version					
BGU8L1UK		wafer level chip-size package; 6 balls; 0.65 $\times$ 0.44 $\times$ 0.29 mm	WLCSP6					

### 4. Marking

#### Table 4.Marking codes

Type number	Marking code
BGU8L1UK	single character, indicating assembly month.[1]

[1] Month code see <u>Table 5</u>.

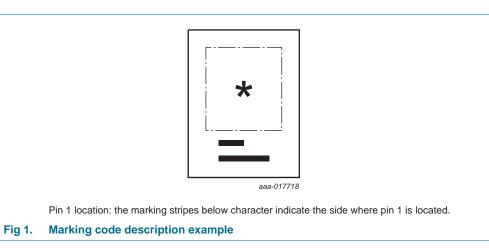
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#### Table 5. Calender marking month code

Asterisk (\*) in Figure 1 is replaced by character in table.

Year [1]	Month											
	J	F	М	Α	М	J	J	Α	S	0	N	D
2014	Y	Z	b	d	f	h	3	4	5	6	7	9
2015	А	В	С	D	E	F	G	Н	I	J	K	L
2016	М	N	0	Ρ	Q	R	S	Т	U	V	W	Х

[1] Rotates every 3 years.



# 5. Limiting values

#### Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage	RF input AC coupled	<u>[1]</u>	-0.5	+5.0	V
V <sub>I(ENABLE)</sub>	input voltage on pin ENABLE	$V_{I(ENABLE)} < V_{CC} + 0.6 V$	[1][2]	-0.5	+5.0	V
$V_{I(RF_IN)}$	input voltage on pin RF_IN	DC, $V_{I(RF_{IN})} < V_{CC} + 0.6 V$	[1][2]	-0.5	+5.0	V
V <sub>I(RF_OUT)</sub>	input voltage on pin RF_OUT	DC, $V_{I(RF_OUT)} < V_{CC} + 0.6 V$	[1][2][3]	-0.5	+5.0	V
Pi	input power		[1]	-	10	dBm
P <sub>tot</sub>	total power dissipation	$T_{sp} \le 130 \ ^{\circ}C$		-	55	mW
T <sub>stg</sub>	storage temperature			-65	+150	°C
Tj	junction temperature			-	150	°C
V <sub>ESD</sub>	electrostatic discharge voltage	Human Body Model (HBM) According to ANSI/ESDA/JEDEC standard JS-001		-	±2	kV
		Charged Device Model (CDM) According to JEDEC standard JESD22-C101C		-	±1	kV

[1] Stressed with pulses of 200 ms in duration.

[2] Warning: due to internal ESD diode protection, the applied DC voltage shall not exceed V<sub>CC</sub> + 0.6 V and shall not exceed 5.0 V in order to avoid excess current.

[3] The RF output is AC coupled through internal DC blocking capacitors.

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# 6. Recommended operating conditions

Table 7.	Operating conditions					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CC</sub>	supply voltage		1.5	-	3.1	V
T <sub>amb</sub>	ambient temperature		-40	+25	+85	°C
V <sub>I(ENABLE)</sub>	input voltage on pin ENABLE	OFF state	-	-	0.3	V
		ON state	0.8	-	-	V

# 7. Thermal characteristics

Та	able 8.	Thermal characteristics			
S	Symbol	Parameter	Conditions	Тур	Unit
F	R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		225	K/W

# 8. Characteristics

#### Table 9. Characteristics at V<sub>CC</sub> = 1.8 V

728 MHz  $\leq$  f  $\leq$  960 MHz; V<sub>CC</sub> = 1.8 V; V<sub>I(ENABLE)</sub>  $\geq$  0.8 V; T<sub>amb</sub> = 25 °C; input matched to 50  $\Omega$  using a 18 nH inductor; unless otherwise specified.

Symbol	Parameter	Conditions	Mi	ו Typ	Max	Unit
I <sub>CC</sub>	supply current	$V_{I(ENABLE)} \ge 0.8 V$	-	4.3	-	mA
		$V_{I(ENABLE)} \leq 0.3 V$	-	-	1	μΑ
G <sub>p</sub>	power gain	f =740 MHz	<u>[1]</u> -	16.5	-	dB
		f = 882 MHz	[2] _	16.0	-	dB
		f = 943 MHz	[3] _	15	-	dB
RL <sub>in</sub>	input return loss	f =740 MHz	<u>[1]</u> -	8	-	dB
		f = 882 MHz	[2] _	9	-	dB
		f = 943 MHz	[3] _	8	-	dB
RL <sub>out</sub>	output return loss	f =740 MHz	<u>[1]</u> -	12	-	dB
		f = 882 MHz	[2] _	12	-	dB
		f = 943 MHz	[3] _	12	-	dB
ISL	isolation	f =740 MHz	<u>[1]</u> -	25	-	dB
		f = 882 MHz	[2] _	25	-	dB
		f = 943 MHz	[3] -	25	-	dB
NF	noise figure	f =740 MHz	<u>[1][4]</u> _	0.7	-	dB
		f = 882 MHz	[2][4] _	0.7	-	dB
		f = 943 MHz	[3][4] _	0.8	-	dB
P <sub>i(1dB)</sub>	input power at 1 dB	f =740 MHz	<u>[1]</u> -	-12	-	dBm
	gain compression	f = 882 MHz	[2] _	-10	-	dBm
		f = 943 MHz	[3] _	-9	-	dBm

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Table 9.Characteristics at V<sub>CC</sub> = 1.8 V ...continued728 MHz  $\leq f \leq$  960 MHz; V<sub>CC</sub> = 1.8 V; V<sub>I(ENABLE)</sub>  $\geq$  0.8 V; T<sub>amb</sub> = 25 °C; input matched to 50  $\Omega$  using a 18 nH inductor; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
IP3 <sub>i</sub>	input third-order intercept point	f =740 MHz	[1]	-	-6	-	dBm
		f = 882 MHz	[2]	-	-4	-	dBm
		f = 943 MHz	[3]	-	-3	-	dBm
К	Rollett stability factor			1	-	-	
t <sub>on</sub>	turn-on time	time from $V_{I(ENABLE)}$ ON, to 90 % of the gain		-	-	3	μs
t <sub>off</sub>	turn-off time	time from $V_{I(ENABLE)}$ OFF, to 10 % of the gain		-	-	1	μs

[1] E-UTRA operating band 17 (734 MHz to 746 MHz).

[2] E-UTRA operating band 5 (869 MHz to 894 MHz).

[3] E-UTRA operating band 8 (925 MHz to 960 MHz).

[4] PCB losses are subtracted

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Table 10.Characteristics at V<sub>CC</sub> = 2.8 V728 MHz  $\leq f \leq 960$  MHz; V<sub>CC</sub> = 2.8 V; V<sub>I(ENABLE)</sub>  $\geq 0.8$  V; T<sub>amb</sub> = 25 °C; input matched to 50  $\Omega$  using a 18 nH inductor; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CC</sub>	supply current	$V_{I(ENABLE)} \ge 0.8 V$		-	4.7	-	mA
		$V_{I(ENABLE)} \le 0.3 V$		-	-	1	μΑ
G <sub>p</sub>	power gain	f =740 MHz	[1]	-	16.5	-	dB
		f = 882 MHz	[2]	-	16.0	-	dB
		f = 943 MHz	[3]	-	15.5	-	dB
RL <sub>in</sub>	input return loss	f =740 MHz	[1]	-	8	-	dB
		f = 882 MHz	[2]	-	10	-	dB
		f = 943 MHz	[3]	-	8	-	dB
RL <sub>out</sub>	output return loss	f =740 MHz	[1]	-	12	-	dB
		f = 882 MHz	[2]	-	12	-	dB
		f = 943 MHz	[3]	-	12	-	dB
ISL	isolation	f =740 MHz	<u>[1]</u>	-	25	-	dB
		f = 882 MHz	[2]	-	25	-	dB
		f = 943 MHz	[3]	-	25	-	dB
NF	noise figure	f =740 MHz	[1][4]	-	0.7	-	dB
		f = 882 MHz	[2][4]	-	0.7	-	dB
		f = 943 MHz	[3][4]	-	0.8	-	dB
P <sub>i(1dB)</sub>	input power at 1 dB	f =740 MHz	[1]	-	-7	-	dBm
	gain compression	f = 882 MHz	[2]	-	-6	-	dBm
		f = 943 MHz	[3]	-	-5	-	dBm
IP3 <sub>i</sub>	input third-order intercept point	f =740 MHz	[1]	-	-1	-	dBm
		f = 882 MHz	[2]	-	2	-	dBm
		f = 943 MHz	[3]	-	1	-	dBm
К	Rollett stability factor			1	-	-	
t <sub>on</sub>	turn-on time	time from $V_{I(\text{ENABLE})}$ ON, to 90 % of the gain		-	-	3	μS
t <sub>off</sub>	turn-off time	time from V <sub>I(ENABLE)</sub> OFF, to 10 % of the gain		-	-	1	μs

[1] E-UTRA operating band 17 (734 MHz to 746 MHz).

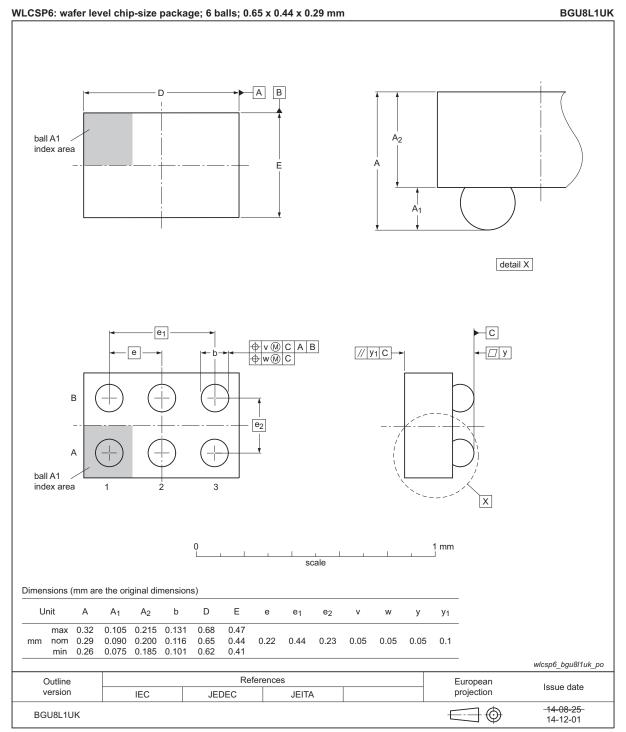
[2] E-UTRA operating band 5 (869 MHz to 894 MHz).

[3] E-UTRA operating band 8 (925 MHz to 960 MHz).

[4] PCB losses are subtracted

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# 9. Package outline



#### Fig 2. Package outline BGU8L1UK (WLCSP6)

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BGU8L1UK

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# **10. Handling information**

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

# **11. Abbreviations**

Table 11. Abbreviations						
Acronym	Description					
ESD	ElectroStatic Discharge					
E-UTRA	Evolved Universal Terrestrial Radio Access					
HBM	Human Body Model					
LTE	Long Term Evolution					
MMIC	Monolithic Microwave Integrated Circuit					
PCB	Printed Circuit Board					
SiGe:C	Silicon Germanium Carbon					

# **12. Revision history**

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU8L1UK v.1	20150519	Product data sheet	-	-

SiGe:C Low Noise Amplifier MMIC for LTE

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
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